



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Inventor: Yukihiro INOUE

Group Art Unit: 2811

Appln. No.: 09/768,556

Examiner: S. Gebremariam

Filed: January 25, 2001

For: SEMICONDUCTOR DEVICE

AMENDMENT UNDER 37 CFR § 1.111

Assistant Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated January 30, 2003,
please amend the above-captioned application as follows:

IN THE CLAIMS:

Please amend the claims as follows (Exhibit I contains a
marked up version):

11. (Twice Amended) A semiconductor device according to
claim 13, wherein said transistor is a high voltage transistor
having a source diffusion layer within said source side offset
diffusion layer region and a drain diffusion layer within said
drain side offset diffusion layer region and said source side
offset diffusion layer and said drain side offset diffusion layer
have impurity concentrations lower than those of said source
diffusion layer and said drain diffusion layer.

#16/Dw/attach

4/30/03

Shm tk

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